1 Characteristics

Symbol	Parameter	Value	Unit		
1			T _c = 108 °C	16	А
I _{T(RMS)}	On-state rms current (full sine wave)		T _c = 119 °C	12	A
1	Non repetitive surge peak on-state current (full	F = 50 Hz	t = 20 ms	120	А
ITSM		F = 60 Hz	t = 16.7 ms	126	A
l ^² t	I ² t Value for fusing		t _p = 10 ms	95	A ² s
V _{DRM} ,	Depetitive pack off state voltage, gate apen	T _j = 150 °C	600	V	
V _{RRM}	Repetitive peak off-state voltage, gate open	T _j = 125 °C	800	v	
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$		T _j = 25 °C	900	V
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ F = 100 Hz				A/µs
I _{GM}	Peak gate current $t_p = 20 \ \mu s$			4	А
P _{G(AV)}	Average gate power dissipation			1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			-40 to +150 -40 to +150	°C
TL	Lead temperature for soldering during 10 s (at 4 mm from case for TO220AB-ins.)			260	°C
V _{ins} (rms)	Insulation rms voltage, 1 minute, TO220AB ceramic insulated			2500	V

Table 2. Absolute maximum rating (T_i = 25 °C, unless otherwise specified)



Table 5.	Electrical characteristics $(1_j = 25 \text{ C}, \text{ unless otherwise specified})$					
Symbol	Test conditions		Quadrant		Value	Unit
ı (1)	$I_{GT}^{(1)}$ $V_{D} = 12 \text{ V}, \text{ R}_{L} = 30 \Omega$		- -	MIN.	0.5	mA
'GT ` ′			- -	MAX.	10	mA
V _{GT}	VD = 12 V, RL = 30 Ω		All	MAX.	1.3	V
V_{GD}	$V_D = 800 \text{ V}, \text{ R}_L = 3.3 \text{ k}\Omega, \text{ T}_j = 125 ^\circ\text{C}$		All	MIN.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA			MAX.	25	mA
۱L	1 1.21	-	MAX.	20	mA	
	$I_{G} = 1.2 I_{GT}$	Ш		30		
dV/dt ⁽¹⁾	$\label{eq:V_D} \begin{array}{ll} V_{D} = 67\% \ x \ 800 \ V \ gate \ open & T_{j} = 125 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{ll} V_{D} = 67\% \ x \ 600 \ V \ gate \ open & T_{j} = 150 \ ^{\circ}\text{C} \end{array}$			MIN.	100	V/µs
uv/ul ()/				IVIIIN.	50	v/µs
	(dV/dt)c = 0.1 V/µs	T _j = 125 °C			9	
(dl/dt)c ⁽¹⁾	(dV/dt)c = 10 V/µs	T _j = 125 °C		MIN.	3	A/ms
	$(dV/dt)c = 0.1 V/\mu s T_j = 150 \ ^{\circ}C$			WIIN.	5.4	A/ms
	(dV/dt)c = 10 V/µs	T _j = 150 °C		1	1.8	
t _{GT}	gate controlled turn on time I _{TM} = 13 A, V _D = 400 V, I _G = 100 mA, dI _G /dt = 100 mA/ μ s, R _L = 30 Ω		- -	TYP.	2	μs

 Table 3.
 Electrical characteristics (T_i = 25 °C, unless otherwise specified)

1. For both polarities of A2 referenced to A1

Table 4.Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM} ⁽¹⁾	I _{TM} = 22.6 A, t _p = 380 μs	T _j = 25 °C	MAX.	1.55	V
V _{to} ⁽¹⁾	Threshold voltage	T _j = 150 °C	MAX.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	MAX.	30	mΩ
	V _{DRM} = V _{RRM} = 800 V	T _j = 25 °C	MAX.	5	μA
I _{DRM} I _{RRM}		T _j = 125 °C		1	μ
	$V_{DRM} = V_{RRM} = 600 V$	T _j = 150 °C		3.6	mA

1. for both polarities of A2 referenced to A1

Table 5.Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	2.1	°C/W
R _{th(j-a)}	Junction to ambient	60	°C/W



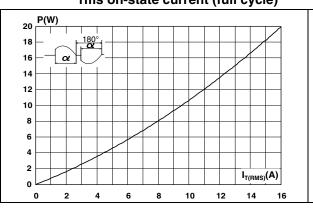
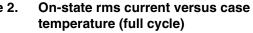
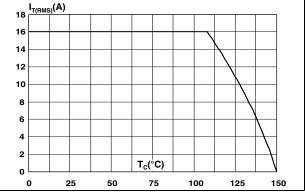


Figure 1. Maximum power dissipation versus Figure 2. rms on-state current (full cycle)





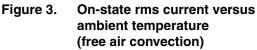
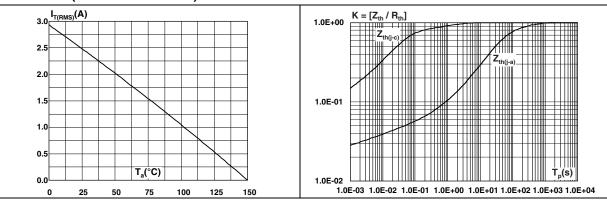


Figure 4. Relative variation of thermal impedance versus pulse duration



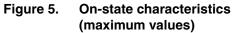


Figure 6. Surge peak on-state current versus number of cycles

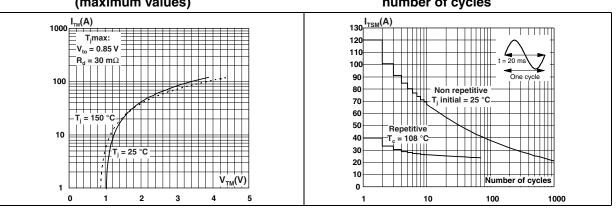




Figure 7. Non repetitive surge peak on-state Figure 8. current and corresponding values of I²t

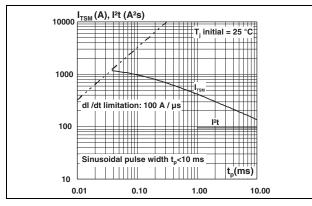


Figure 9. Relative variation of gate trigger voltage versus junction temperature (typical values)

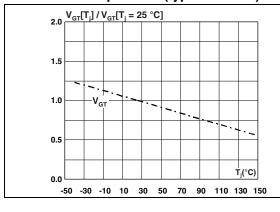
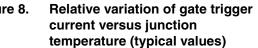


Figure 11. Relative variation of critical rate of Figure 12. decrease of current (dl/dt)c versus reapplied (dV/dt)c



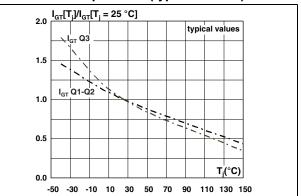
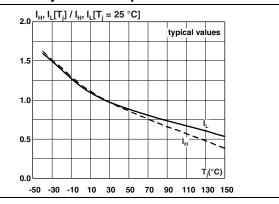
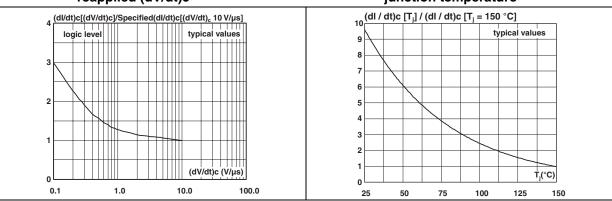


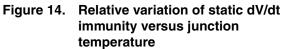
Figure 10. Relative variation of holding current and latching current versus junction temperature



Relative variation of critical rate of decrease of current (dl/dt)c versus junction temperature







T1610T-8I

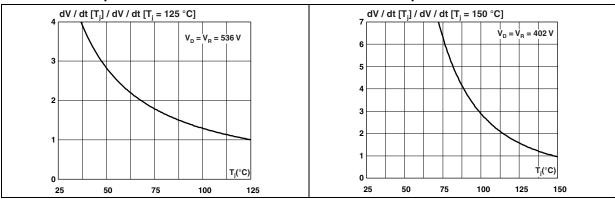
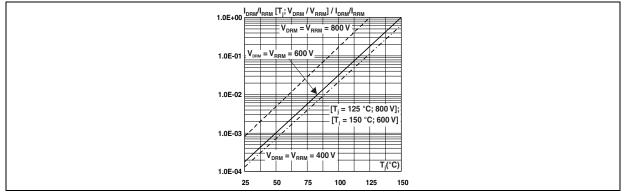


Figure 15. Relative variation of leakage current versus junction temperature for different values of blocking voltage





2 Package information

- Epoxy meets UL94, V0
- Recommended torque value: 0.4 to 0.6 N·m

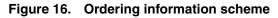
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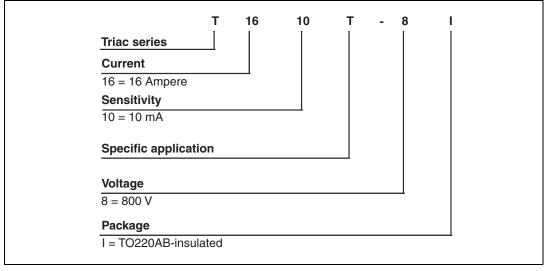
Table 6. TO-220AB insulated dimensions

					Dimer	nsions			
				Millimeters			Inches		
			Min.	Тур.	Max.	Min.	Тур.	Max.	
		А	15.20		15.90	0.598		0.625	
		a1		3.75			0.147		
Ø I	C C	a2	13.00		14.00	0.511		0.551	
	<u>b2</u> ,	В	10.00		10.40	0.393		0.409	
	F	b1	0.61		0.88	0.024		0.034	
A		b2	1.23		1.32	0.048		0.051	
		С	4.40		4.60	0.173		0.181	
	c2	c1	0.49		0.70	0.019		0.027	
	←→ _	c2	2.40		2.72	0.094		0.107	
		е	2.40		2.70	0.094		0.106	
	M	F	6.20		6.60	0.244		0.259	
 e ^{→++} • b1		ØI	3.75		3.85	0.147		0.151	
		14	15.80	16.40	16.80	0.622	0.646	0.661	
		L	2.65		2.95	0.104		0.116	
		12	1.14		1.70	0.044		0.066	
		13	1.14		1.70	0.044		0.066	
		М		2.60			0.102		



3 Ordering information scheme







4 Ordering information

Table 7.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1610T-8I	T1610T-8I	TO-220AB insulated	2.3	50	Tube

5 Revision history

Table 8.Document revision history

Date	Revision	Changes	
08-Aug-2011	1	First issue.	
20-Jan-2012	2	Corrected subscripting error in Table 3.	



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